

2N7002W, 2V7002W

Small Signal MOSFET

60 V, 340 mA, Single, N-Channel, SC-70

Features

- ESD Protected
- Low $R_{DS(on)}$
- Small Footprint Surface Mount Package
- 2V Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Low Side Load Switch
- Level Shift Circuits
- DC-DC Converter
- Portable Applications i.e. DSC, PDA, Cell Phone, etc.

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	60	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Drain Current (Note 1) Steady State	I_D	$T_A = 25^\circ\text{C}$	310
		$T_A = 85^\circ\text{C}$	220
$t < 5$ s		$T_A = 25^\circ\text{C}$	340
		$T_A = 85^\circ\text{C}$	240
Power Dissipation (Note 1) Steady State $t < 5$ s	P_D		280
			330
Pulsed Drain Current ($t_p = 10 \mu\text{s}$)	I_{DM}	1.4	A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode)	I_S	250	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$
Gate-Source ESD Rating (HBM, Method 3015)	ESD	2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	450	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 5$ s (Note 1)	$R_{\theta JA}$	375	

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)

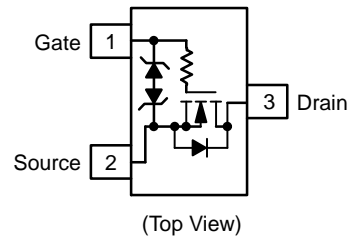


ON Semiconductor®

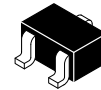
www.onsemi.com

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX (Note 1)
60 V	1.6 Ω @ 10 V	340 mA
	2.5 Ω @ 4.5 V	

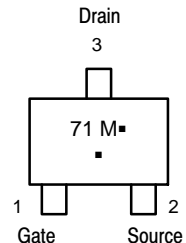
SIMPLIFIED SCHEMATIC



MARKING DIAGRAM & PIN ASSIGNMENT



SC-70/SOT-323
CASE 419
STYLE 8



71 = Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
2N7002WT1G	SC-70 (Pb-Free)	3000/Tape & Reel
2V7002WT1G	SC-70 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

2N7002W, 2V7002W

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			71		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 150^\circ\text{C}$		15	μA
		$V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}$	$T_J = 25^\circ\text{C}$		100	nA
			$T_J = 150^\circ\text{C}$		10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 10	μA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$			450	nA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 5.0\text{ V}$			150	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.0		2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			4.0		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 500\text{ mA}$		1.19	1.6	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 200\text{ mA}$		1.33	2.5	
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 200\text{ mA}$		530		mS

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 20\text{ V}$		24.5		pF
Output Capacitance	C_{OSS}			4.2		
Reverse Transfer Capacitance	C_{RSS}			2.2		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 10\text{ V}; I_D = 200\text{ mA}$		0.7		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.1		
Gate-to-Source Charge	Q_{GS}			0.3		
Gate-to-Drain Charge	Q_{GD}			0.1		

SWITCHING CHARACTERISTICS, $V_{GS} = V$ (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DD} = 25\text{ V}, I_D = 500\text{ mA}, R_G = 25\ \Omega$		12.2		ns
Rise Time	t_r			9.0		
Turn-Off Delay Time	$t_{d(OFF)}$			55.8		
Fall Time	t_f			29		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 200\text{ mA}$	$T_J = 25^\circ\text{C}$		0.8	1.2	V
			$T_J = 85^\circ\text{C}$		0.7		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$

3. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

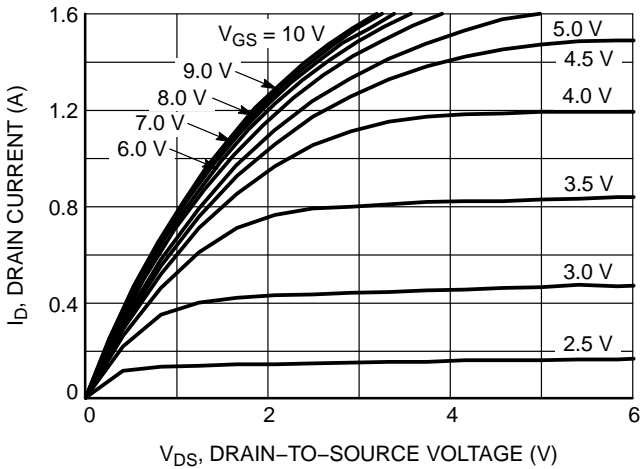


Figure 1. On-Region Characteristics

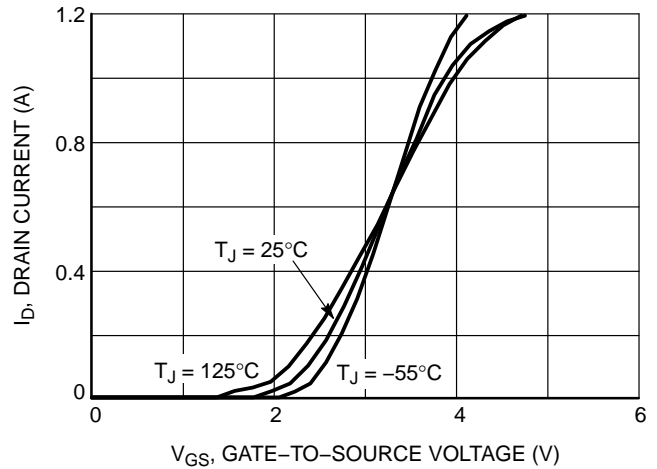


Figure 2. Transfer Characteristics

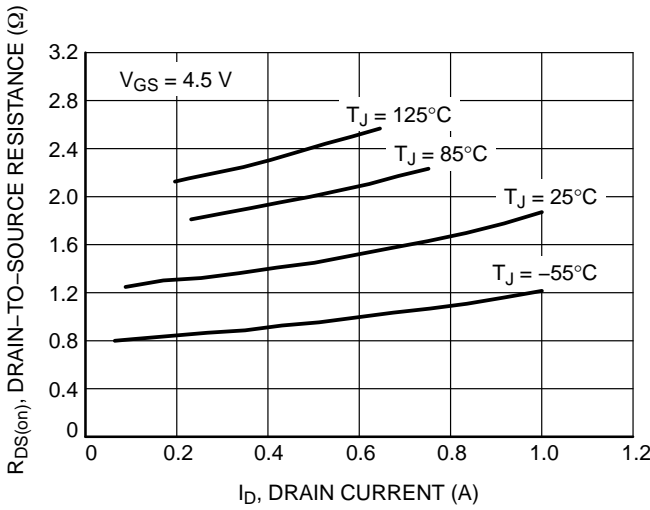


Figure 3. On-Resistance vs. Drain Current and Temperature

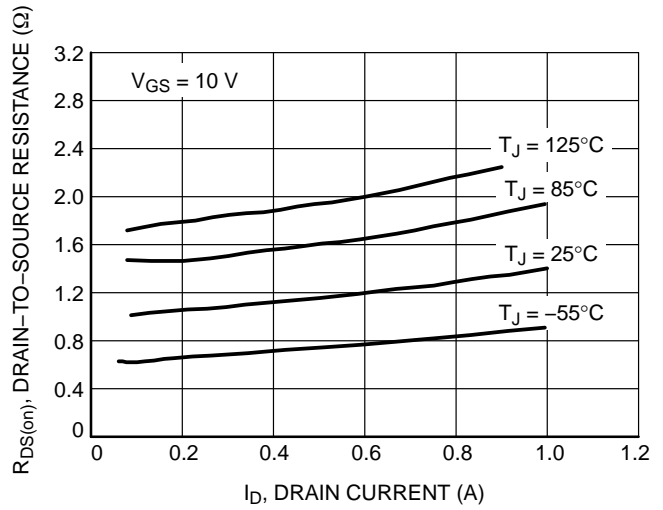


Figure 4. On-Resistance vs. Drain Current and Temperature

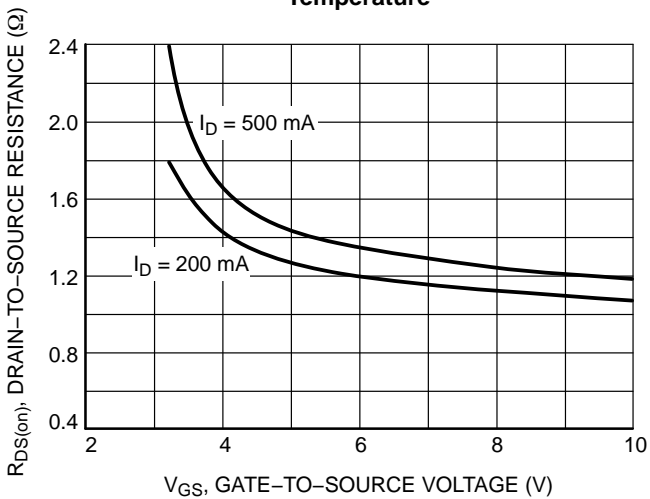


Figure 5. On-Resistance vs. Gate-to-Source Voltage

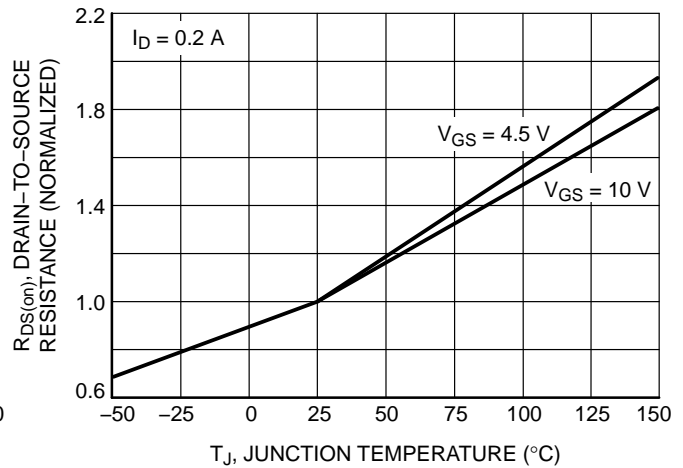


Figure 6. On-Resistance Variation with Temperature

2N7002W, 2V7002W

TYPICAL CHARACTERISTICS

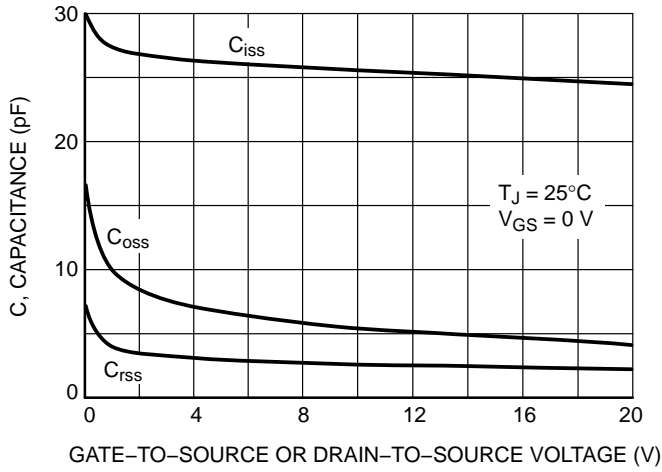


Figure 7. Capacitance Variation

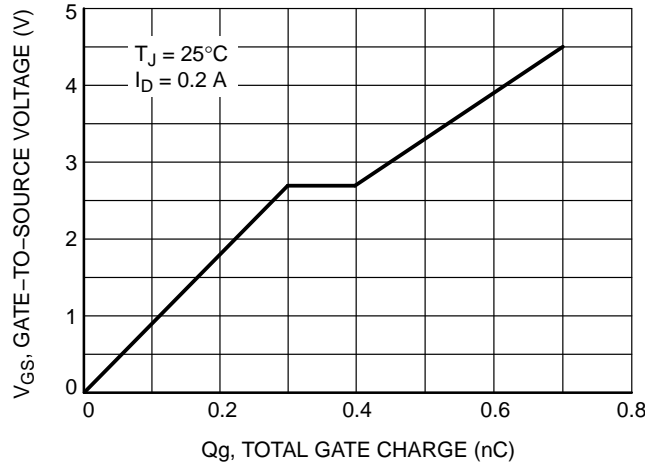


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

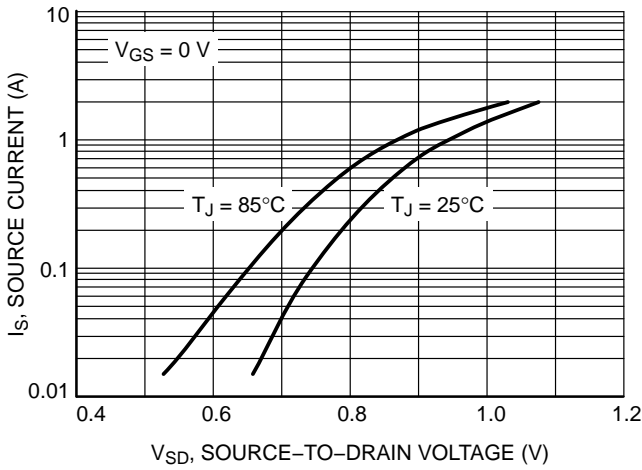


Figure 9. Diode Forward Voltage vs. Current

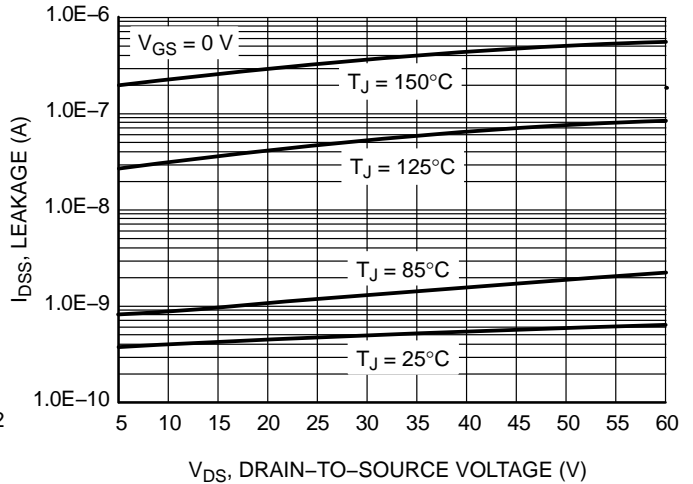
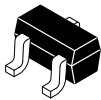


Figure 10. Drain-to-Source Leakage Current vs. Voltage

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

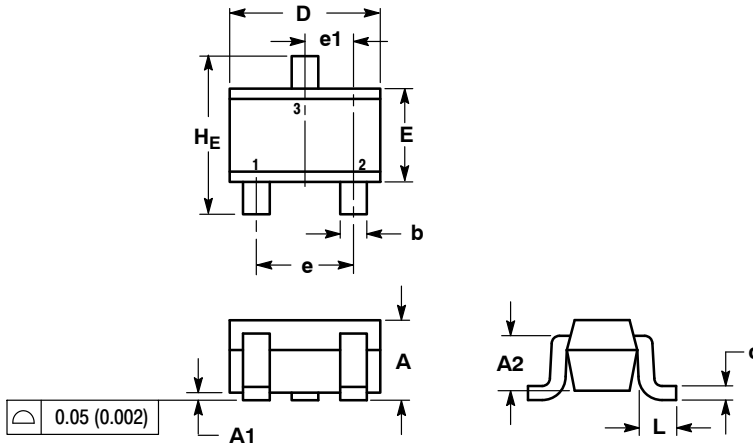
ON Semiconductor®



SCALE 4:1

SC-70 (SOT-323)
CASE 419-04
ISSUE N

DATE 11 NOV 2008

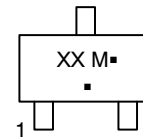


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

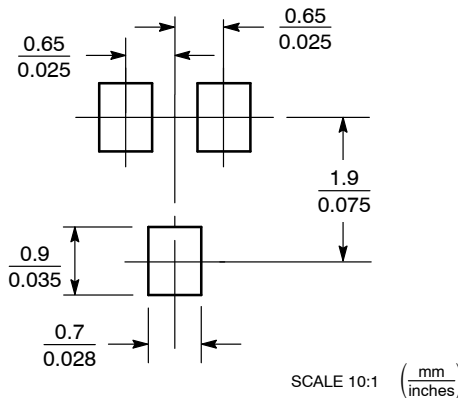
GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 7: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 8: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 9: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 10: PIN 1. CATHODE 2. ANODE 3. ANODE-CATHODE	STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:
Voice Mail: 1 800-282-9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative